Dr. R. Srinivasan Professor/ IT Department Sri Sivasubramaniya Nadar College of Engineering Rajiv Gandhi Salai (OMR) Kalavakkam Chennai - 603110

Mail ID: srinivasanr@ssn.edu.in

Mob. No: 9444446747

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- **15.** G Durga, and R Srinivasan, "Silicon Nanotube SRAM and its SEU Reliability" Superlattices and Microstructures (Elsevier Publisher), Vol. 106, 2017, 129-138.
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